



#### 20V P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

| V <sub>(BR)DSS</sub> | R <sub>DS(ON) max</sub>        | Package | I <sub>D max</sub><br>T <sub>A</sub> = +25°C |
|----------------------|--------------------------------|---------|--|
| -20V                 | 60mΩ @ V <sub>GS</sub> = -4.5V | SOT-23  | -4.0A  |
| -20V                 | 90mΩ @ V <sub>GS</sub> = -2.5V | 501-23  | -3.3A  |

#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The DMP2065UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

## **Description and Applications**

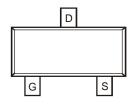
This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(on)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

#### **Mechanical Data**

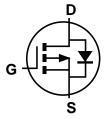
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 63
- Lead-Free Plating (Matte Tin Finish Annealed over Alloy 42 Lead-Frame).
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



Top View



Top View Pin Configuration



**Equivalent Circuit** 

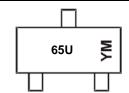
## **Ordering Information** (Note 4)

| Part Number  | Case  | Packaging          |
|--------------|-------|--------------------|
| DMP2065UQ-7  | SOT23 | 3000/Tape & Reel   |
| DMP2065UQ-13 | SOT23 | 10,000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



65U = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020)M = Month (ex: 9 = September)

Date Code Key

| Year  | 202 | 0   | 2021 |     | 2022 | 20  | 23       | 2024 |     | 2025 | 2   | 2026 |
|-------|-----|-----|------|-----|------|-----|----------|------|-----|------|-----|------|
| Code  | Н   |     | I    |     | J    | -   | <b>(</b> | L    |     | M    |     | N    |
| Month | Jan | Feb | Mar  | Apr | May  | Jun | Jul      | Aug  | Sep | Oct  | Nov | Dec  |
| Code  | 1   | 2   | 3    | 4   | 5    | 6   | 7        | 8    | 9   | 0    | N   | D    |



### **Maximum Ratings** (@ T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic  |            |                  | Symbol          | Value        | Units |
|---|------------|------------------|-----------------|--------------|-------|
| Drain-Source Voltage  |            |                  | $V_{DSS}$       | -20          | V     |
| Gate-Source Voltage   |            | V <sub>GSS</sub> | ±12             | V            |       |
| Drain Current (Note 6) Vgs= -4.5V Steady $T_A = +25^{\circ}C$<br>State $T_A = +70^{\circ}C$ |            |                  | I <sub>D</sub>  | -4.0<br>-3.0 | Α     |
| Pulsed Drain Current (Pulse width ≤10µS, Duty C   | Cycle ≤1%) |                  | I <sub>DM</sub> | -15          | A     |

### **Thermal Characteristics**

| Characteristic                                   |              | Symbol          | Value       | Unit |
|--|--------------|-----------------|-------------|------|
| Total Power Dissipation (Note 5)                 |              | $P_{D}$         | 0.9         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | $R_{	hetaJA}$   | 138         | °C/W |
| Total Power Dissipation (Note 6)                 |              | P <sub>D</sub>  | 1.5         | W    |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | $R_{	hetaJA}$   | 83          | °C/W |
| Operating and Storage Temperature Range          |              | $T_{J,}T_{STG}$ | -55 to +150 | °C   |

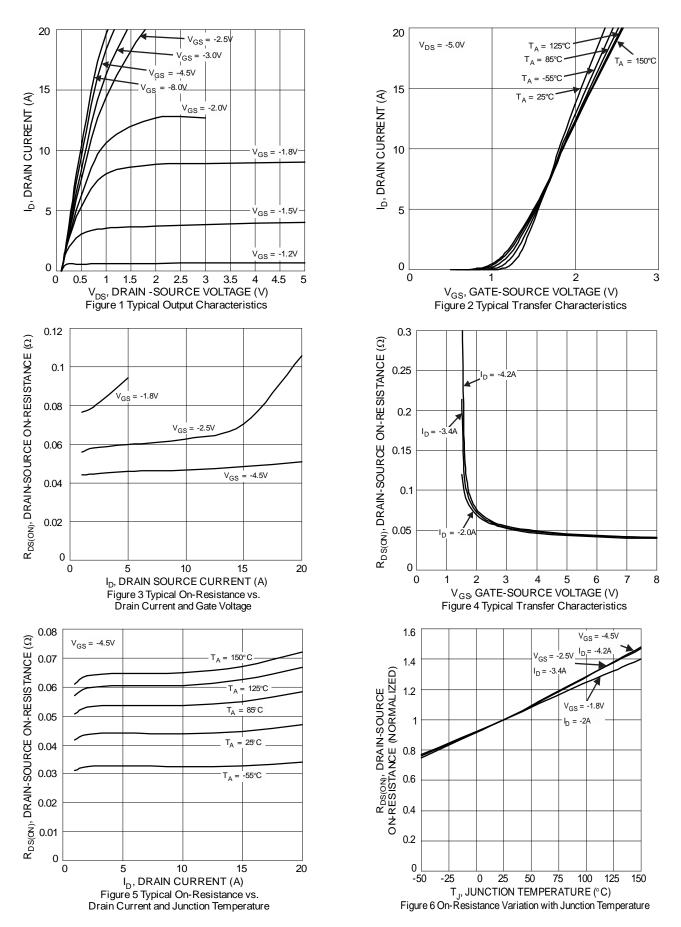
# **Electrical Characteristics** (@ T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic                                 | Symbol               | Min  | Тур  | Max  | Unit | Test Condition                                      |  |
|--|----------------------|------|------|------|------|---|--|
| OFF CHARACTERISTICS (Note 7)                   |                      |      |      |      |      |   |  |
| Drain-Source Breakdown Voltage                 | $BV_{DSS}$           | -20  | _    | _    | V    | $V_{GS} = 0V, I_D = -250\mu A$                      |  |
| Zero Gate Voltage Drain Current $T_J = +25$ °C | I <sub>DSS</sub>     | _    | _    | -1.0 | μA   | $V_{DS} = -20V, V_{GS} = 0V$                        |  |
| Gate-Source Leakage                            | I <sub>GSS</sub>     | _    | _    | ±50  | nA   | $V_{GS} = \pm 8V, V_{DS} = 0V$                      |  |
| ON CHARACTERISTICS (Note 7)                    |                      |      |      |      |      |   |  |
| Gate Threshold Voltage                         | V <sub>GS(th)</sub>  | -0.5 | _    | -0.9 | V    | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$               |  |
|  |                      |      | 41   | 60   |      | $V_{GS} = -4.5V$ , $I_{D} = -4.2A$                  |  |
| Static Drain-Source On-Resistance              | R <sub>DS (ON)</sub> | _    | 53   | 90   | mΩ   | $V_{GS} = -2.5V$ , $I_D = -3.4A$                    |  |
|  |                      |      | 72   | 113  |      | $V_{GS} = -1.8V$ , $I_D = -2.0A$                    |  |
| Diode Forward Voltage                          | $V_{SD}$             | _    | -0.7 | -1.1 | V    | $V_{GS} = 0V, I_{S} = -1A$                          |  |
| DYNAMIC CHARACTERISTICS (Note 8)               |                      |      |      |      |      |   |  |
| Input Capacitance                              | Ciss                 | _    | 808  |      | pF   | V 45V V 6V  |  |
| Output Capacitance                             | Coss                 | _    | 85   |      | pF   | $V_{DS} = -15V, V_{GS} = 0V$<br>-f = 1.0MHz         |  |
| Reverse Transfer Capacitance                   | C <sub>rss</sub>     | _    | 77   |      | pF   | 1 = 1.0WH IZ  |  |
| Gate Resistance                                | R <sub>G</sub>       | _    | 15.2 |      | Ω    | $V_{GS} = 0V$ , $V_{DS} = 0V$ , $f = 1.0MHz$        |  |
| Total Gate Charge                              | $Q_g$                | _    | 10.2 |      | nC   |   |  |
| Gate-Source Charge                             | $Q_{gs}$             | _    | 1.3  | _    | nC   | $V_{GS} = -4.5V$ , $V_{DS} = -4V$ , $I_{D} = -3.5A$ |  |
| Gate-Drain Charge                              | $Q_{gd}$             | _    | 2.2  | _    | nC   |   |  |
| Turn-On Delay Time                             | t <sub>D(on)</sub>   | _    | 10.8 | _    | ns   |   |  |
| Turn-On Rise Time                              | t <sub>r</sub>       |      | 13.7 | _    | ns   | $V_{DS} = -4V$ , $V_{GS} = -4.5V$ ,                 |  |
| Turn-Off Delay Time                            | t <sub>D(off)</sub>  |      | 79.3 | _    | ns   | $R_L = 4\Omega$ , $R_G = 6\Omega$ , $I_D = -1A$     |  |
| Turn-Off Fall Time                             | t <sub>f</sub>       |      | 34.7 | _    | ns   |   |  |

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1in. square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







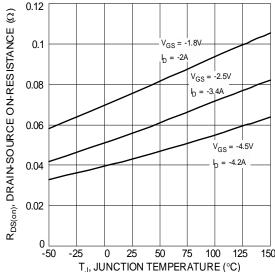
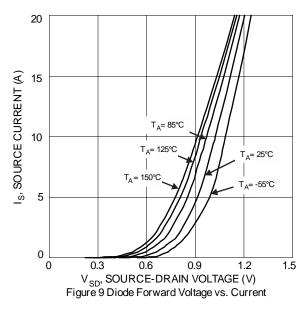
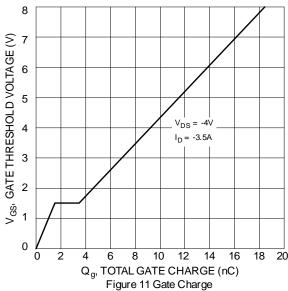


Figure 7 On-Resistance Variation with Junction Temperature





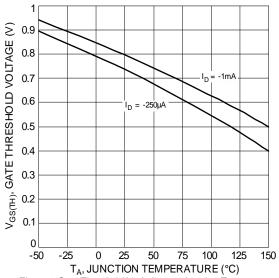
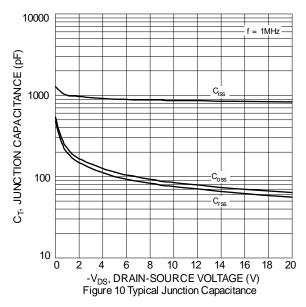
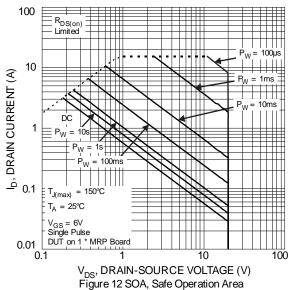
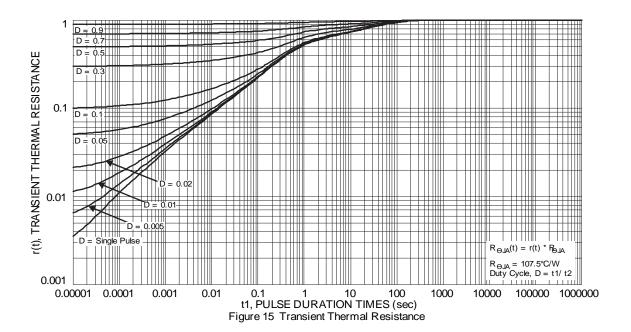


Figure 8 Gate Threshold Variation vs. Junction Temperature







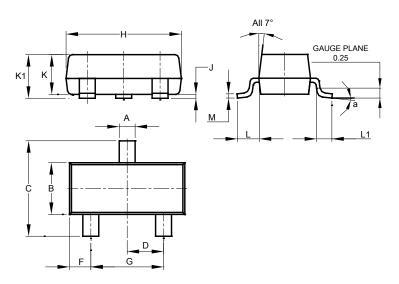




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

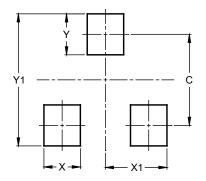


| SOT23                |       |       |       |  |  |  |  |
|----------------------|-------|-------|-------|--|--|--|--|
| Dim                  | Min   | Max   | Тур   |  |  |  |  |
| Α                    | 0.37  | 0.51  | 0.40  |  |  |  |  |
| В                    | 1.20  | 1.40  | 1.30  |  |  |  |  |
| С                    | 2.30  | 2.50  | 2.40  |  |  |  |  |
| D                    | 0.89  | 1.03  | 0.915 |  |  |  |  |
| F                    | 0.45  | 0.60  | 0.535 |  |  |  |  |
| G                    | 1.78  | 2.05  | 1.83  |  |  |  |  |
| Н                    | 2.80  | 3.00  | 2.90  |  |  |  |  |
| J                    | 0.013 | 0.10  | 0.05  |  |  |  |  |
| K                    | 0.890 | 1.00  | 0.975 |  |  |  |  |
| K1                   | 0.903 | 1.10  | 1.025 |  |  |  |  |
| L                    | 0.45  | 0.61  | 0.55  |  |  |  |  |
| L1                   | 0.25  | 0.55  | 0.40  |  |  |  |  |
| М                    | 0.085 | 0.150 | 0.110 |  |  |  |  |
| а                    | 0°    | 8°    |       |  |  |  |  |
| All Dimensions in mm |       |       |       |  |  |  |  |

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



| Dimensions | Value (in mm) |  |  |  |
|------------|---------------|--|--|--|
| С          | 2.0           |  |  |  |
| Х          | 0.8           |  |  |  |
| X1         | 1.35          |  |  |  |
| Y          | 0.9           |  |  |  |
| V4         | 2.0           |  |  |  |



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